

1. (Amended)

B2
Sub
C1 A method of manufacturing a thin film resistor with a moisture barrier comprising:
depositing a metal film layer on a substrate;
attaching a termination on each end of the metal film; and
depositing a layer of tantalum pentoxide film directly overlaying and attaching to the metal film layer.

Please add new claim 15 as follows:

15. (New)

B2
Sub
C2 A method of manufacturing a thin film resistor with a moisture barrier comprising:
depositing a metal film layer on a substrate;
attaching a termination on each end of the metal film;
depositing a passivation layer directly overlaying and attaching to the metal film layer; and
depositing a layer of tantalum pentoxide film directly overlaying and attaching to the passivation layer.